ES2AF THRU ES2JF

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Surface Mount Superfast Recovery Rectifier
Reverse Voltage – 50 to 600 V
Forward Current –2 A

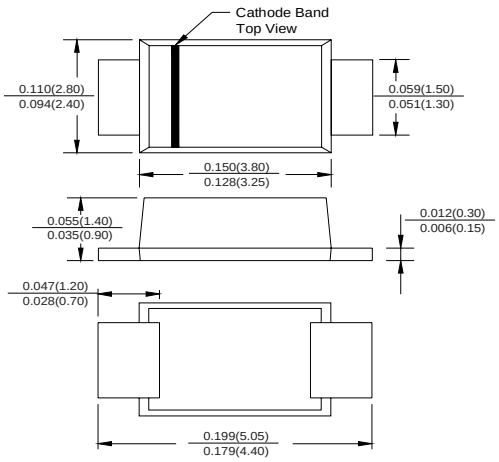
FEATURES

- For surface mounted applications
- Low profile package
- Glass Passivated Chip Juntion
- Superfast reverse recovery time
- Lead free in comply with EU RoHS 2011/65/EU directives

MECHANICAL DATA

- Case: SMAF
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 27mg 0.00086oz

SMAF



Dimensions in inches and (millimeters)

Absolute Maximum Ratings and Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive bad. For capacitive bad, derate current by 20%.

Parameter	Symbols	ES2AF	ES2BF	ES2CF	ES2DF	ES2EF	ES2GF	ES2JF	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	600	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current at T_L = 100 °C	$I_{F(AV)}$	2							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	50							A
Maximum Forward Voltage at 2A	V_F	1				1.25		1.7	V
Maximum DC Reverse Current Ta = 25 °C at Rated DC Blocking Voltage Ta =125 °C	I_R	5 100							μA
Typical Junction Capacitance at V_R=4V, f=1MHz	C_j	60							pF
Maximum Reverse Recovery Time at I_F=0.5A, I_R=1A, I_{rr}=0.25A	t_{rr}	35							ns
Operating and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150							°C

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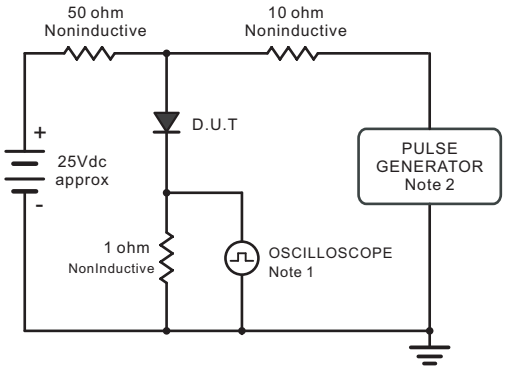
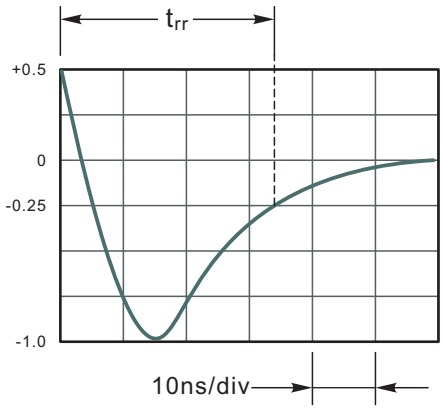
Fig.1 Reverse Recovery Time Characteristic And Test Circuit Diagram



Note: 1. Rise Time = 7ns, max.
Input Impedance = 1megohm,22pF.
2. Ries Time =10ns, max.
Source Impedance = 50 ohms.



Set time Base for 10ns/div

Fig.2 Maximum Average Forward Current Rating

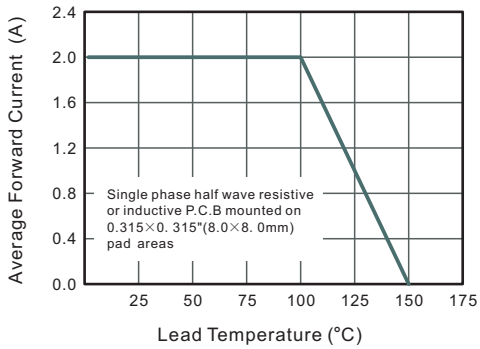


Fig.3 Typical Reverse Characteristics

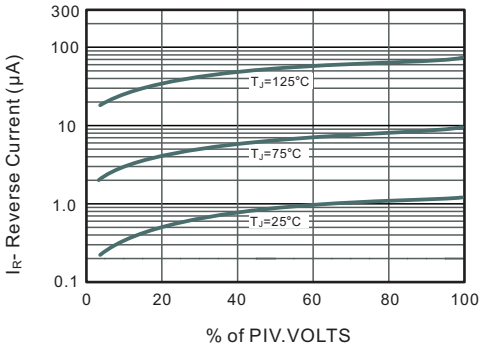


Fig.4 Typical Forward Characteristics

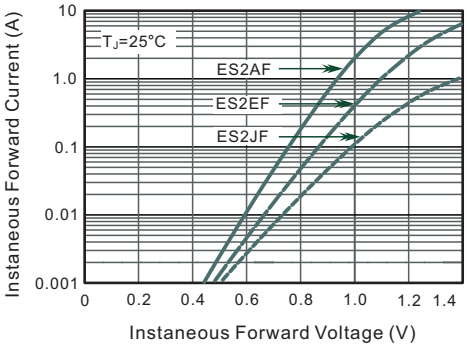
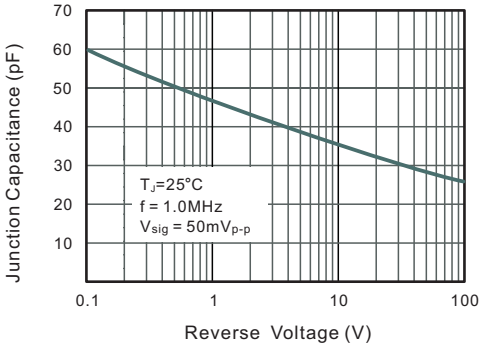



Fig.5 Typical Junction Capacitance